

High resolution Hard X-ray Microscopy at the Advanced Photon Source:

Current capabilities and Future Thrust

*Materials Science with Coherent Nanobeams
at the Edge of Feasibility*

June 27, 2011

Jörg Maser

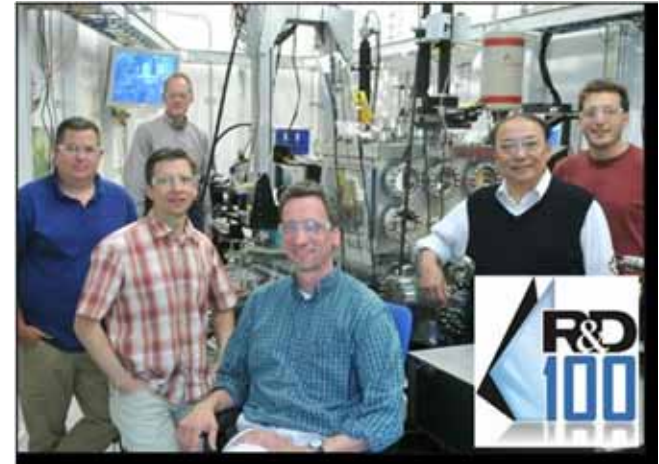
*Advanced Photon Source, Center for Nanoscale Materials
Argonne National Laboratory*



Collaborators

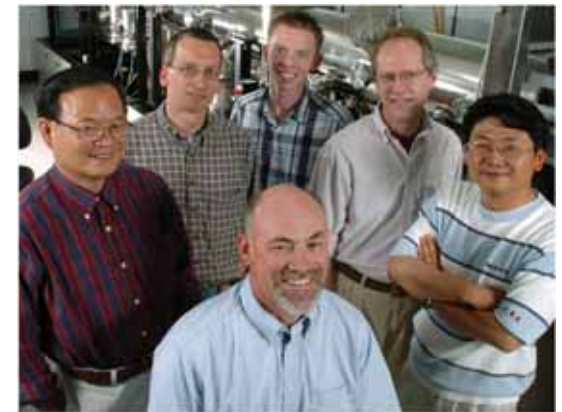
Hard X-ray Nanoprobe (CNM/APS)

R. P. Winarski, M. V. Holt*, R. P. Winarski+, V. Rose, D. Carbaugh**, P. Fuesz, G. B. Stephenson*^{\$}



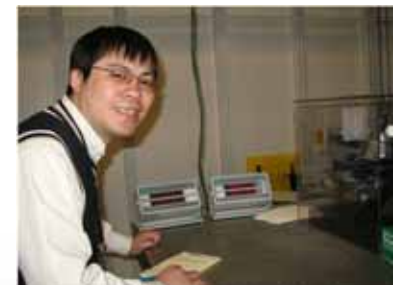
Multilayer Laue Lens

H. Yan^{\$\$}, V. Rose**, R. Conley^{\$\$}, H. C. Kang^{\$}, A. T. Macrander**, R. Conley^{\$\$}, D. Shu**, L. Assoufid**, B. Shi**



In Situ Nanoprobe

B. Lai, T. Buonassisi, D. Barton, W. Chiu, S. Darling, E. Ingall, J. Kang, K. Kemner, G. Mitchell, P. Monteiro, C. Murray, T. Rajh, V. Rose, Z. Cai,¹ I. McNulty, L. Finney, C. Jacobsen, S. Vogt

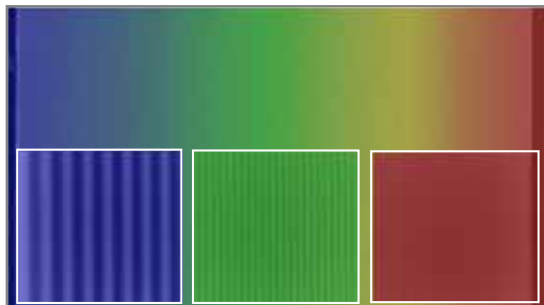
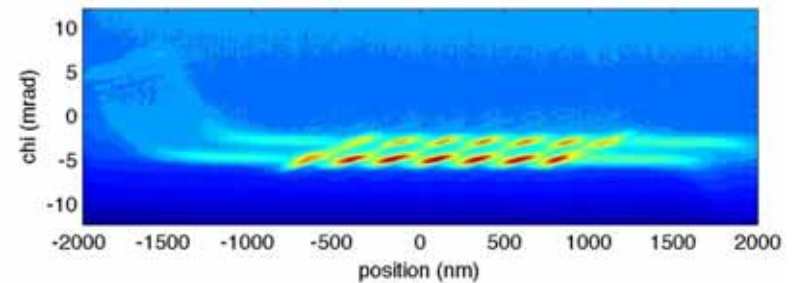
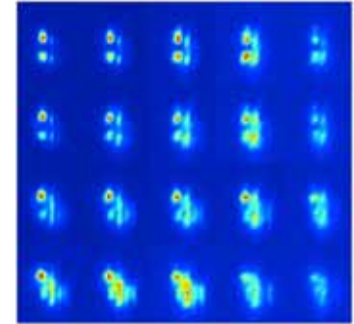


*CNM, **APS, \$MSD, \$\$NSLS-II, ²MIT, ³Dow Chemical Company, ⁴University of Connecticut, ⁵Georgia Institute of Technology, ⁶UC Berkeley, ⁷IBM



Overview

- Motivation: High Resolution Imaging Approaches
- The Hard X-ray Nanoprobe – an Analytical X-ray Microscope
- Towards Nanofocusing of Hard X-rays: Multilayer Laue Lenses
- Outlook: the In-Situ Nanoprobe



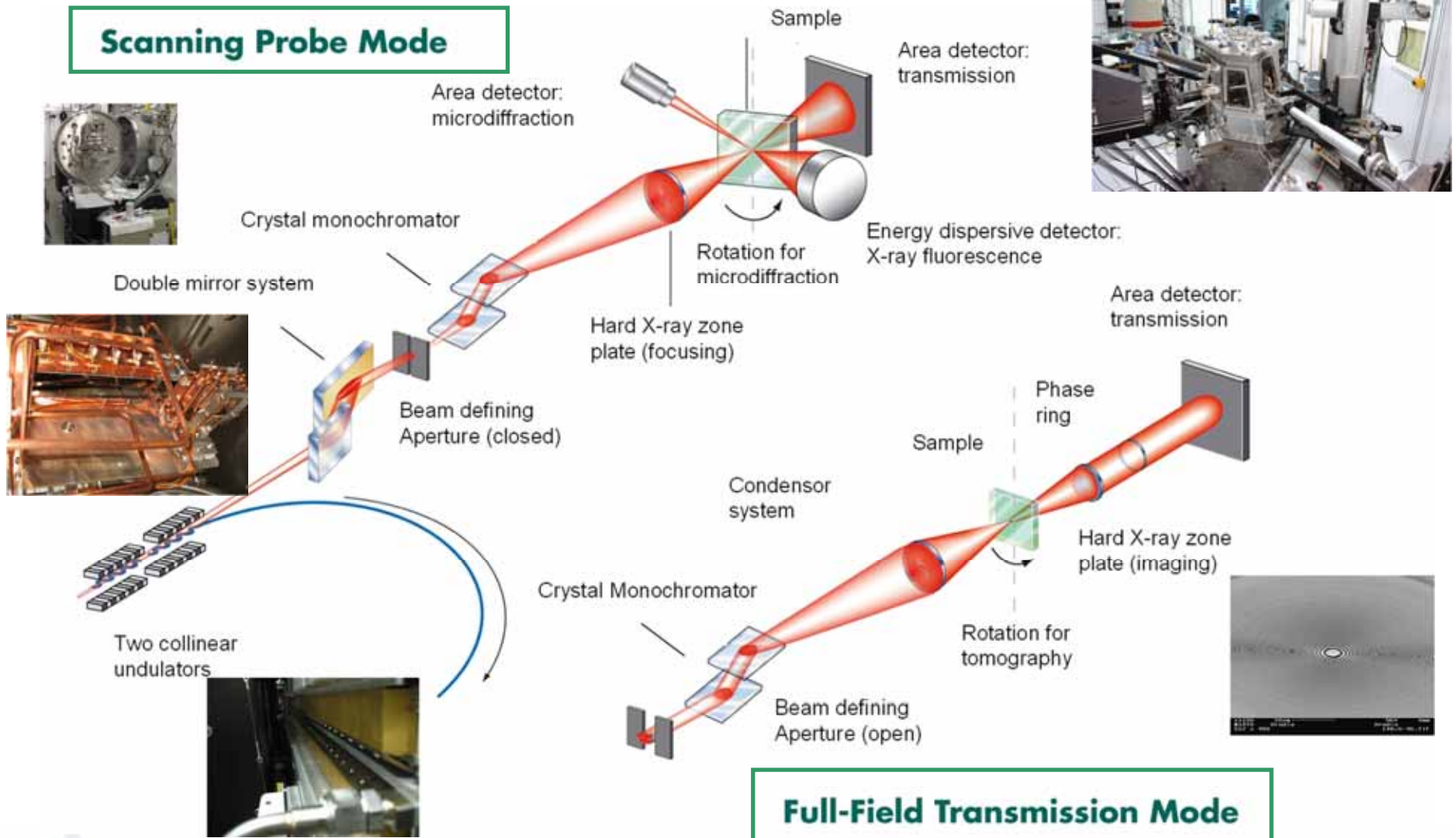
I) High resolution characterization techniques

- Scanning Probe Microscopy: atomic-resolution surface characterization
 - Near-field optical microscopy, Atomic force/magnetic force/piezo force microscopy....
- Electron microscopy: atomic resolution structure/composition characterization
 - TEM, cross sectional TEM, STEM, SEM
- X-ray microscopy: nanoscale resolution structure/composition characterization
 - Properties:
 - Good penetration
 - Insensitive to electric/magnetic fields, environments → in-situ studies
 - Elemental/chemical/phase/strain sensitivity
 - Good time resolution
 - X-ray Scattering: nanosize characterization in environments/fluids
 - Particle size distributions (SAX), Non-uniform surface/interface features (Diffuse scattering)
 - Imaging of isolated, non-periodic systems (coherent)
 - X-ray Imaging:
 - Non-period complex structures with composition/phase/strain sensitivity
 - Use of secondary signals (fluorescence/scattering) from small volumes



CNM/APS Hard X-ray Nanoprobe: Combined Analytic and Imaging Mode

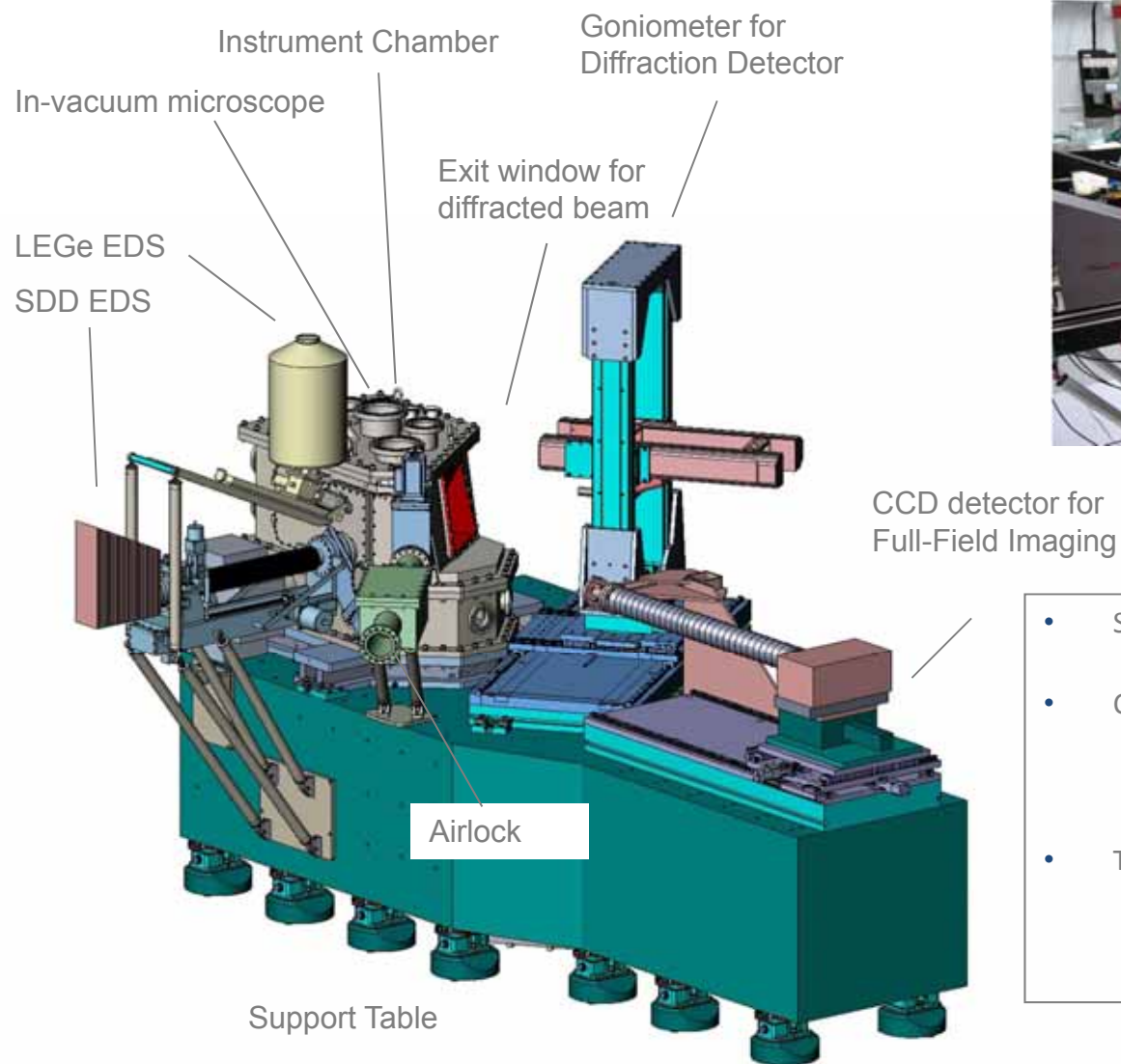
Scanning Probe Mode



Full-Field Transmission Mode



Concept: Integration of 3D Imaging and Analytic Mode



- Scientific Thrust:
 - Materials characterization at the nanoscale
- Capabilities:
 - Photon Energy: 3 – 30 keV
 - Spatial resolution: 30 nm (TXM)
 - 40 nm (scanning)
- Techniques:
 - Diffraction
 - x-ray fluorescence,
 - tomographic transmission imaging

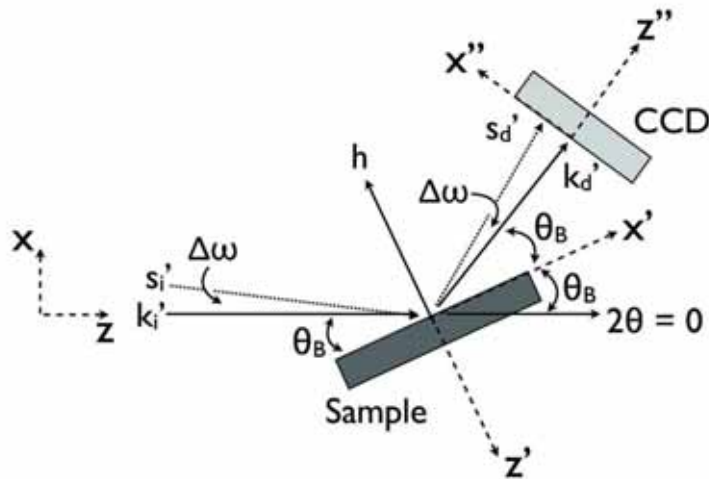
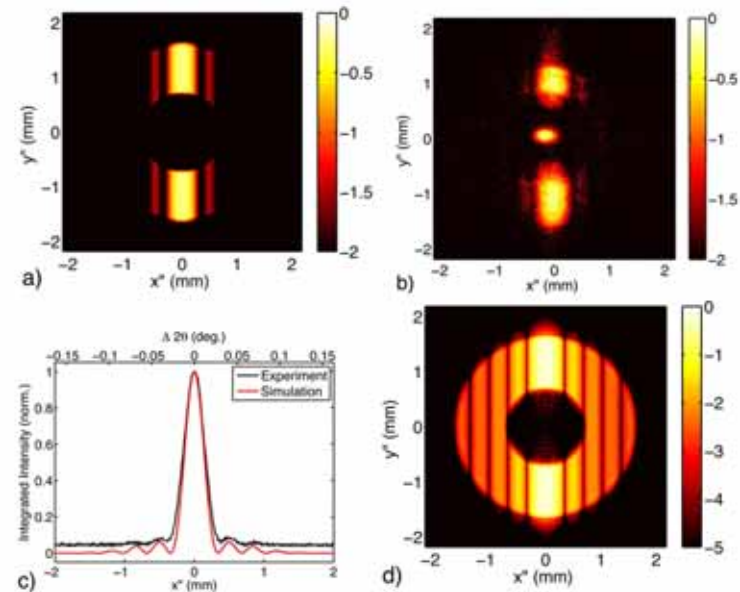
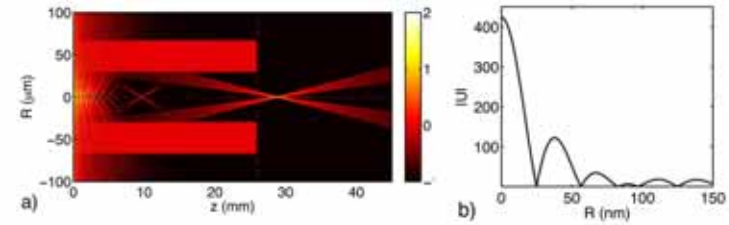
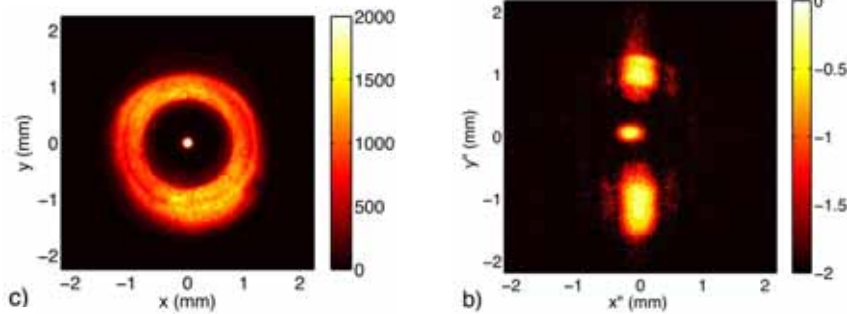
Overall concept and Scanning/Encoding Mechanism: ANL

Engineering Design, Controls, TXM technology and Fabrication: XRADIA, Inc



Nanodiffraction of strained SOI heterostructures

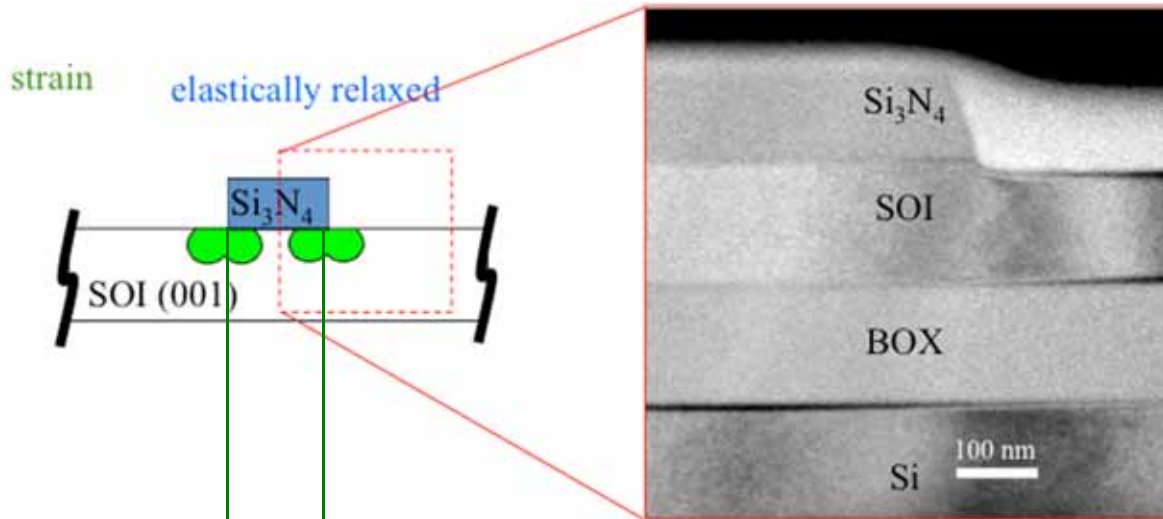
Characterization of nanobeam diffraction with high numerical aperture



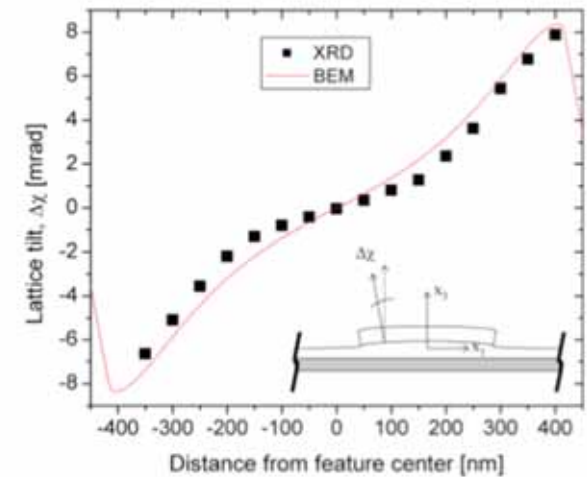
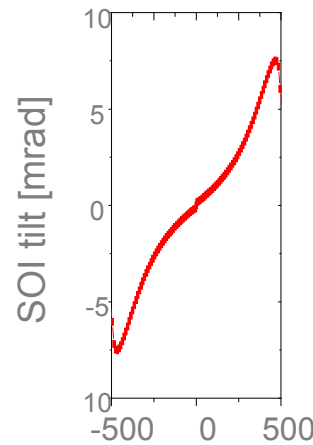
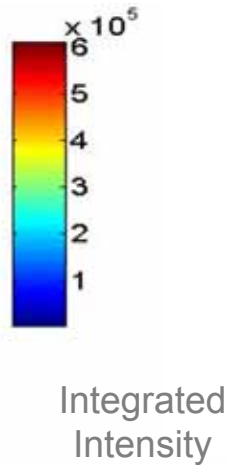
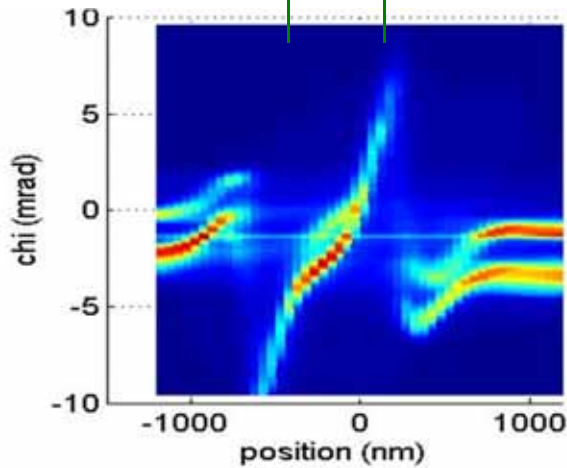
Andrew Ying, Braxton Osting, I.C. Noyan, Conal E. Murray, Martin Holt and Jörg Maser.
 J. Appl. Crystallogr. 43 (3), 587-595 (2010).



Strained silicon for CMOS applications



- antisymmetric lattice tilt distribution observed
- high degree of strain at feature edges
- tilt maxima @ ± 7.5 mrad

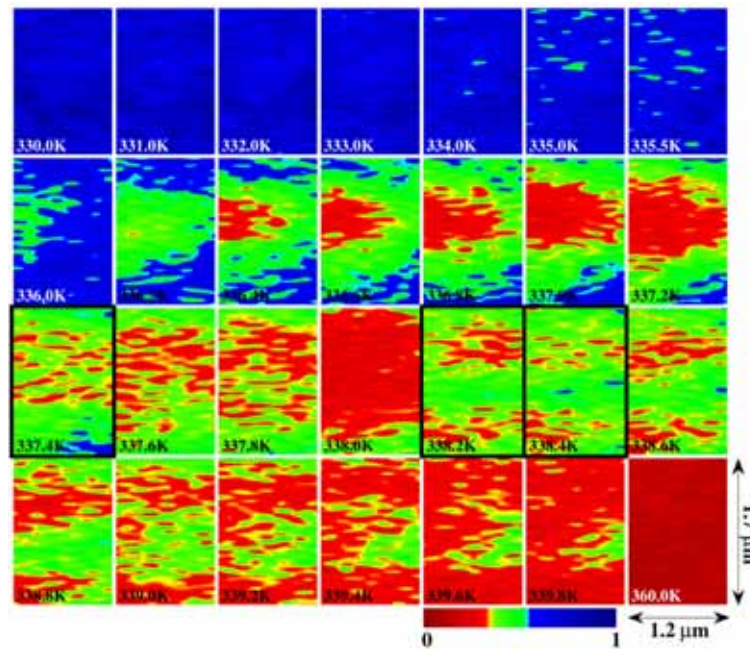


Structural Transitions in VO₂

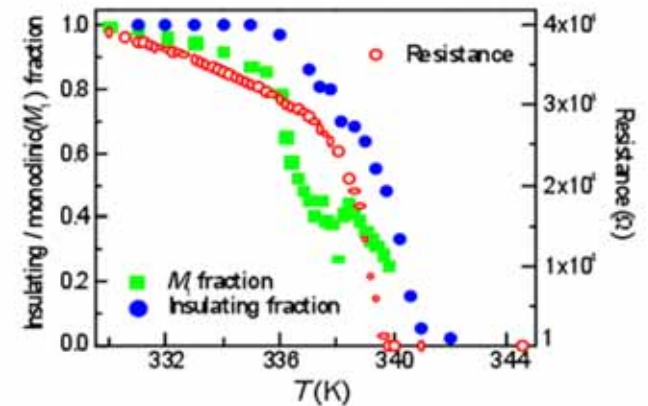
Study metal-to-insulator transition - correlation between structural and electronic phase transitions?

Variation in the intensity of the Bragg peak from the M1 phase of VO₂, $\theta = 29.58^\circ$.

Higher intensities (dark blue) indicate the presence of the M1 phase, lower intensities (red) represent the rutile phase, and intermediate intensities (green color) indicates coexistence of M1 and rutile phases.



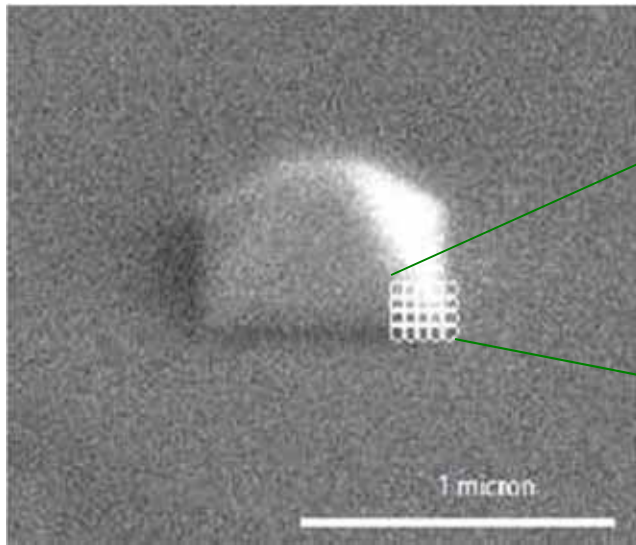
Non-monotonic growth of metallic “puddles”



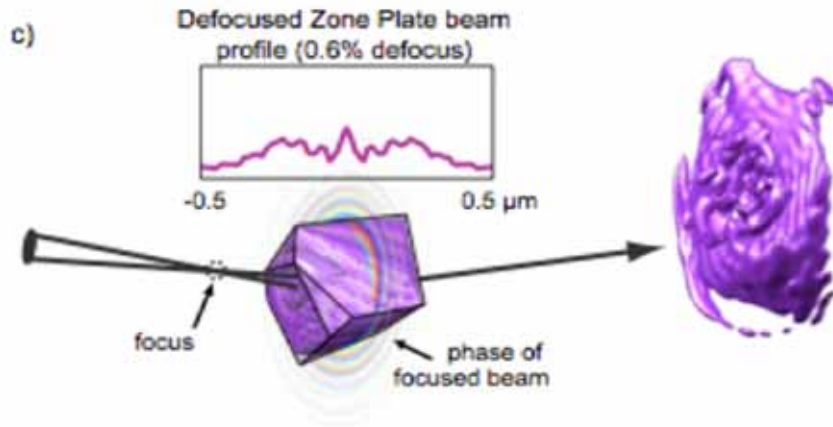
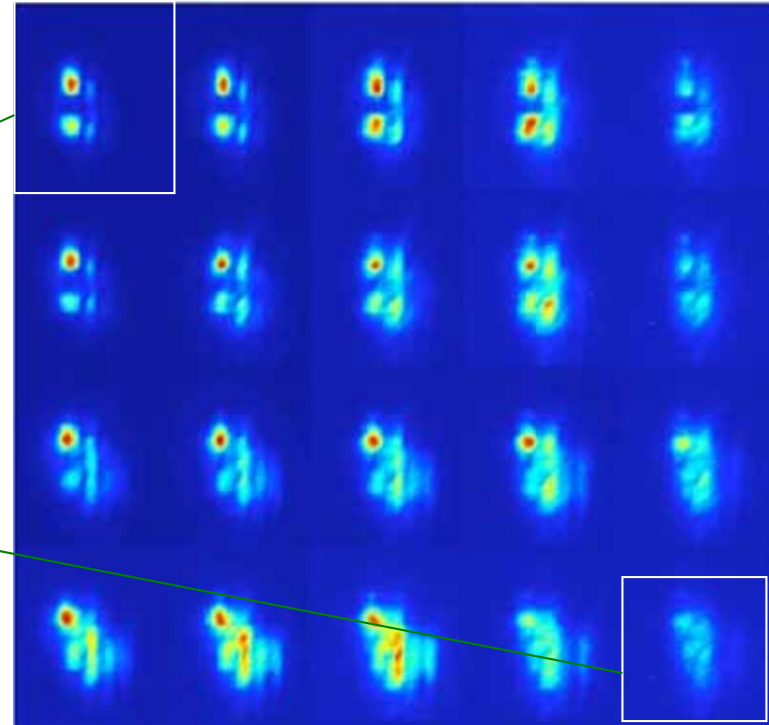
Fraction of monoclinic M_1 phase, resistance of VO₂ vs. temperature



Bragg coherent diffraction in Bragg geometry: from Bi_2O_3 nanoislands



Bi_2O_3 β -phase nanopyramid (SEM).

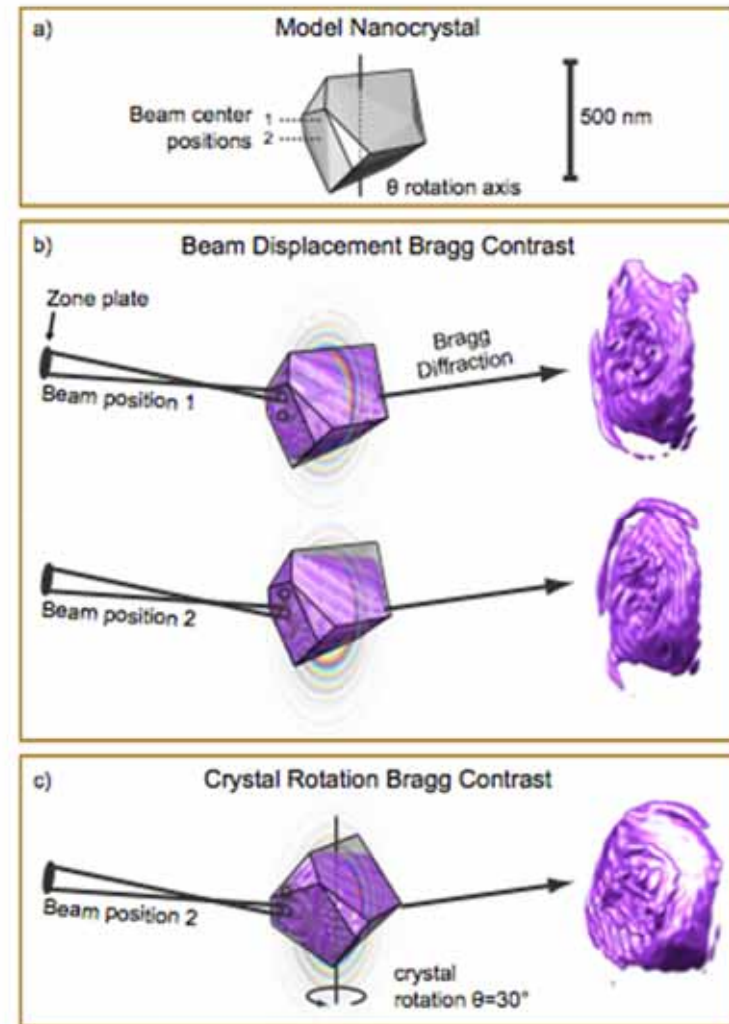
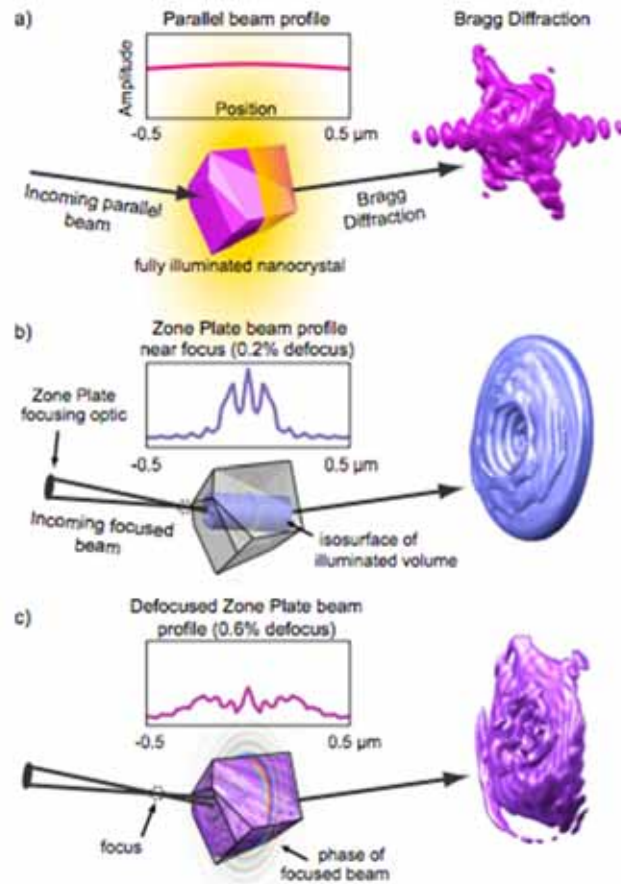


D.L Proffit (MSD-ANL & Northwestern U.); G.-R. Bai, D.D. Fong, T.T. Fister, S. Hruszkewycz, M.J. Highland, P.M. Baldo, P.H. Fuoss, J.A. Eastman (MSD-ANL); T.O. Mason (Northwestern U.)

S. Hruszkewycz, M. V. Holt, A. Tripathi, J. Maser, P. H. Fuoss, *Optics Letters*, Vol. 36, Issue 12, pp. 2227-2229 (2011)



Bragg coherent diffraction from Bi_2O_3 nanoislands

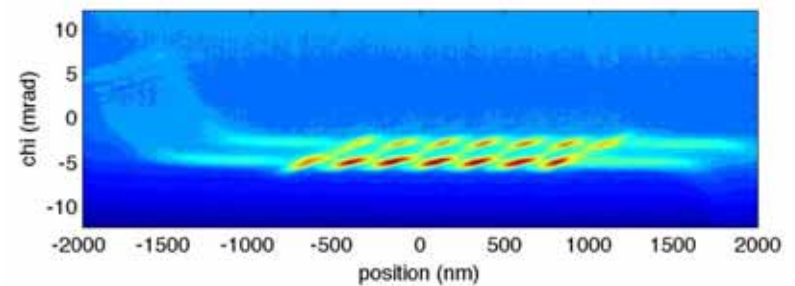
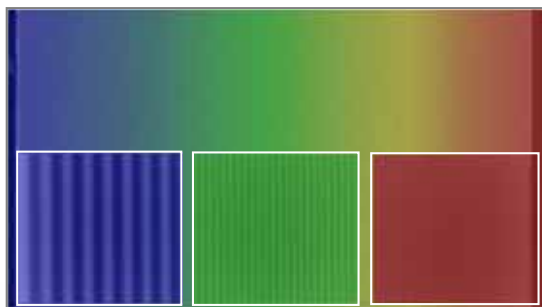
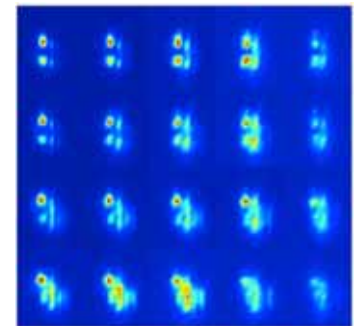


S. Hruszkewycz, M. V. Holt, A. Tripathi, J. Maser, P. H. Fuoss, Optics Letters, Vol. 36, Issue 12, pp. 2227-2229 (2011)



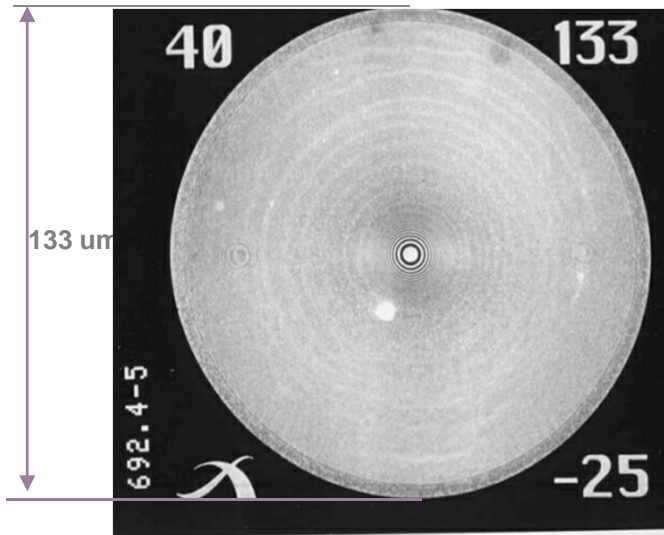
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Diffraction Optics for Focusing and Imaging Optics

- Spatial resolution: ~ 15 nm for soft x-rays (CXRO/BESSY),
 ~ 30 nm – 40 nm for hard x-rays (APS TXM, CNM HXN, 2008)



Critical Parameter: Aspect ratio $A = t/dr_n$

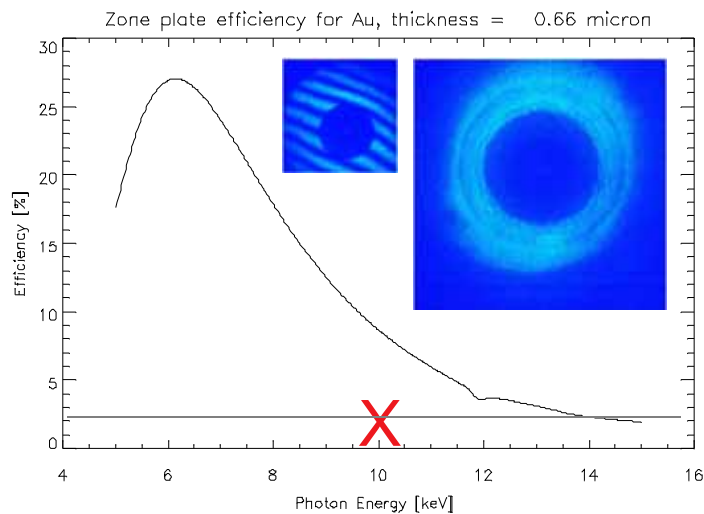
$dr_N = 24$ nm: AR ! 100:1, $E = 10$ keV

E-beam lithography: AR $\cong 10:1 - 15:1$

Currently fabricated, XRADIA:

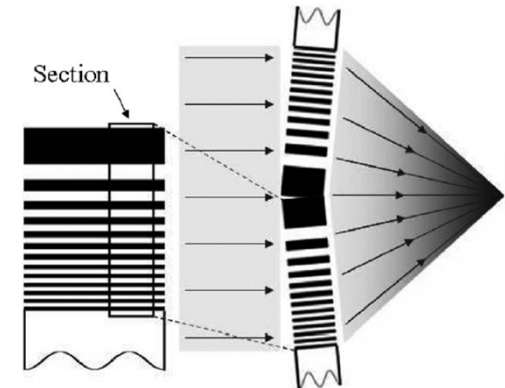
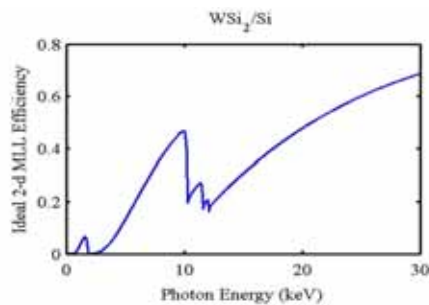
single stack zone plate, $t = 300$ nm

two stacked 24 nm ZP, $t = 660$ nm, $\eta = 2\%$



Path to high resolution and high efficiency:

Multilayer Laue Lens

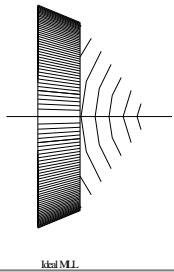


Courtesy G. B. Stephenson

Understanding the Ultimate Resolution Limit

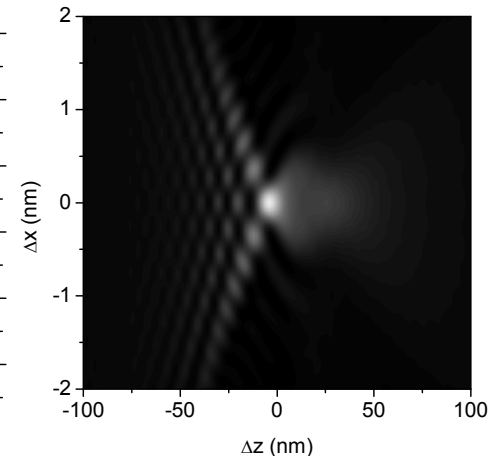
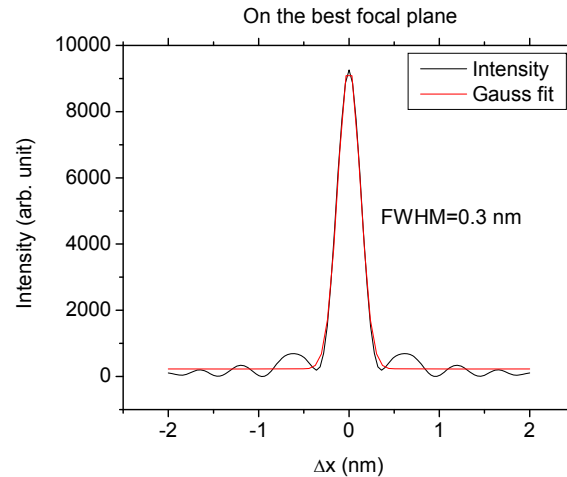
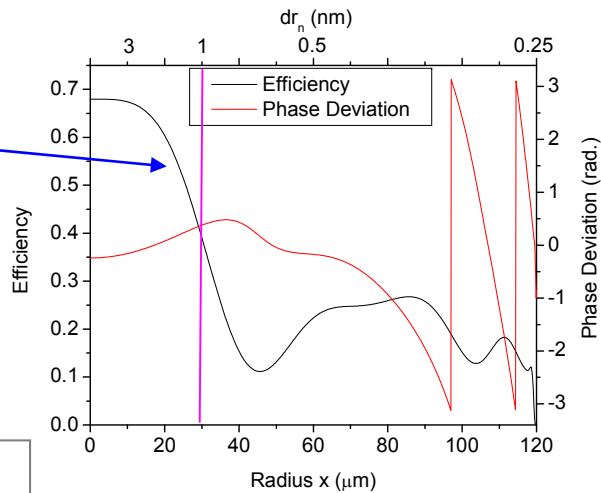
Takagi-Taupin Description of Dynamical Diffraction

Reduced Efficiency at $dr_N \sim 1.5 \text{ nm}$

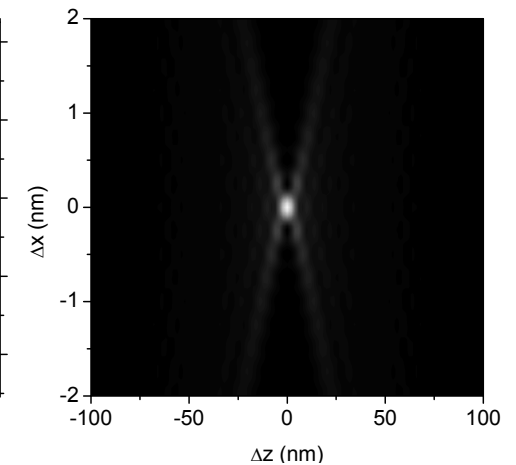
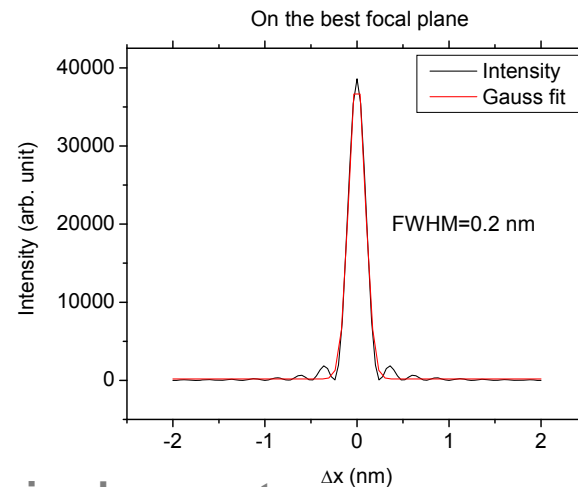
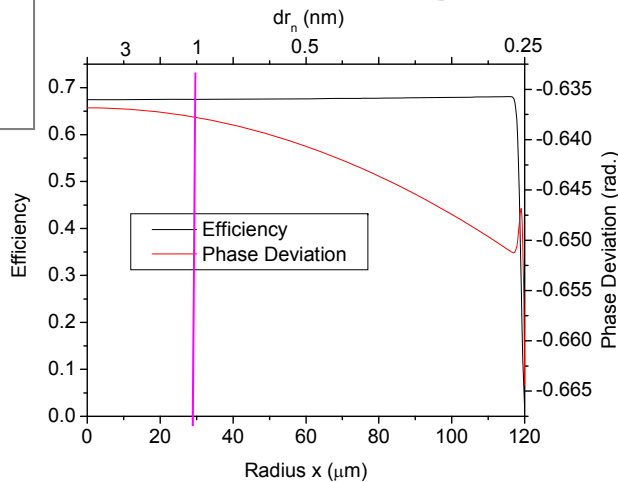


Std MLL

$dr_N = 2.5 \text{ \AA}$
 $E = 19.5 \text{ keV}$
 $D = 120 \text{ \mu m}$
 WSi_2/Si



Wedged MLL, straight zones

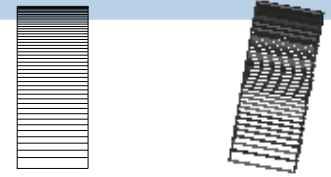


Ideal MLL, optimized geometry

Hanfei Yan et al. (PRB, 2007)



Partial flat/tilted Multilayer Laue Lens

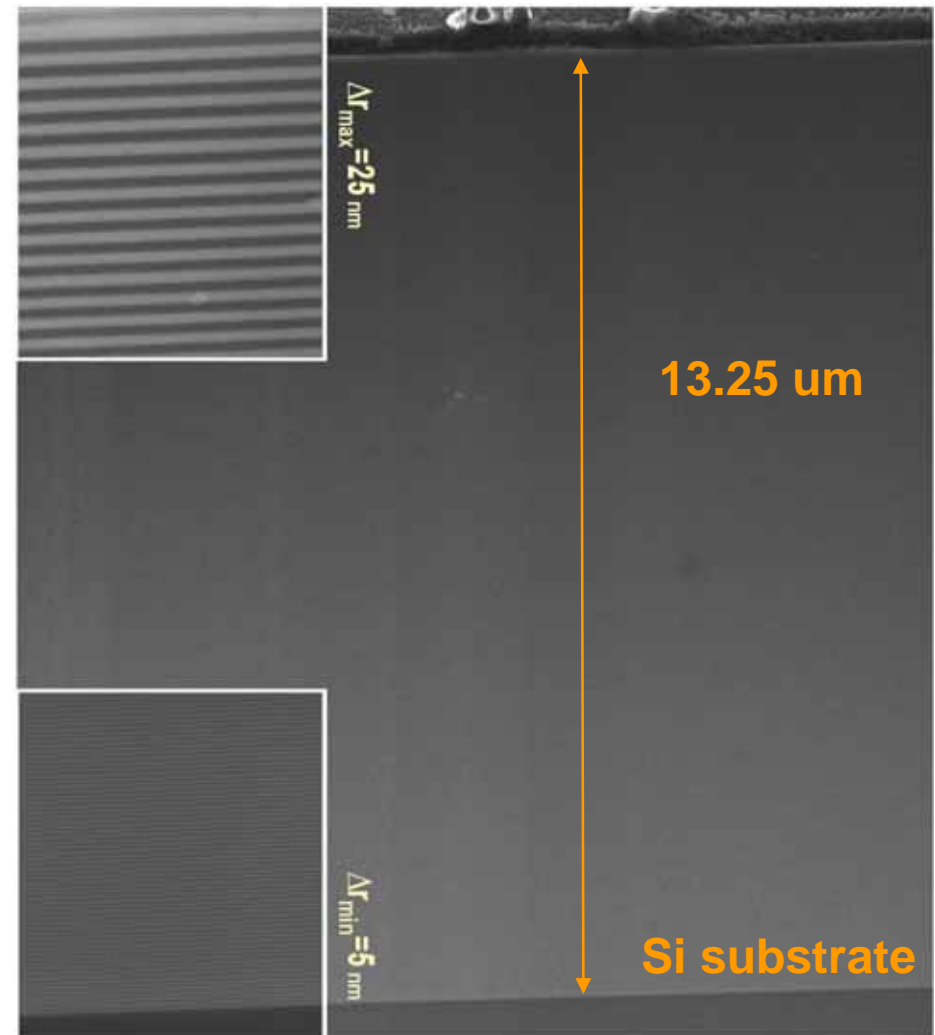


- Example for $dr_N = 5$ nm structure:

- Material: WSi_2/Si
- $dr_N = 5$ nm ($2d = 10$ nm)
- $r_n = 16.5$ μ m (13.3 μ m deposited)
- $N = 1653$ (~ 1588 deposited)
- Usable aperture fraction: 40%

- Challenges:

- Large deposition thickness requires low stress: $\rightarrow WSi_2/Si$
- High accuracy of layer placement:
 - $f = (2 r_n / \lambda) \cdot dr_n(r_n)$
- Thinning/Polishing: avoid distortions of structure



Courtesy R. Conley, C. Liu, A. Macrander

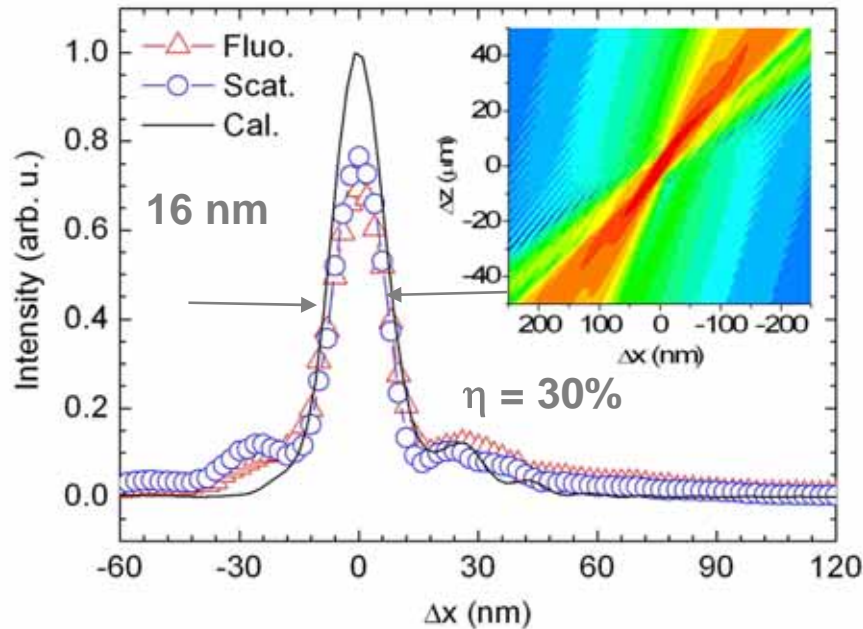


X-ray focusing with tilted MLL sections (1D, 2D), $dr_N = 5 \text{ nm}$

Parameters:

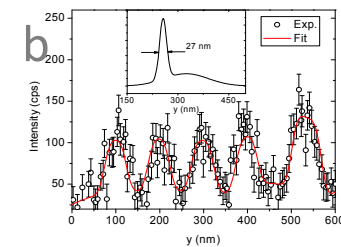
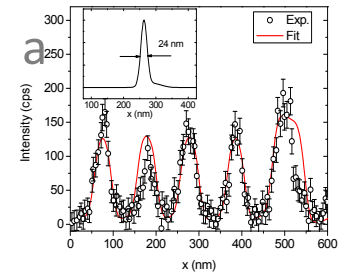
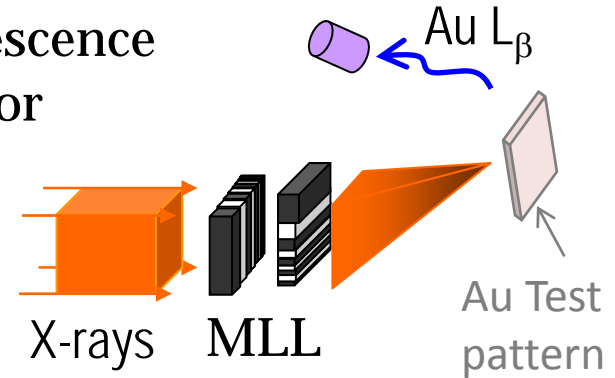
- $dr_N = 5 \text{ nm}$ structure:
- Deposited: $13.3 \text{ }\mu\text{m}$ of $30 \text{ }\mu\text{m}$
- diffraction limit: 12.5 nm

Photon Energy: 19.5 keV



1D Efficiency: 30% at 19.5 keV

Fluorescence detector

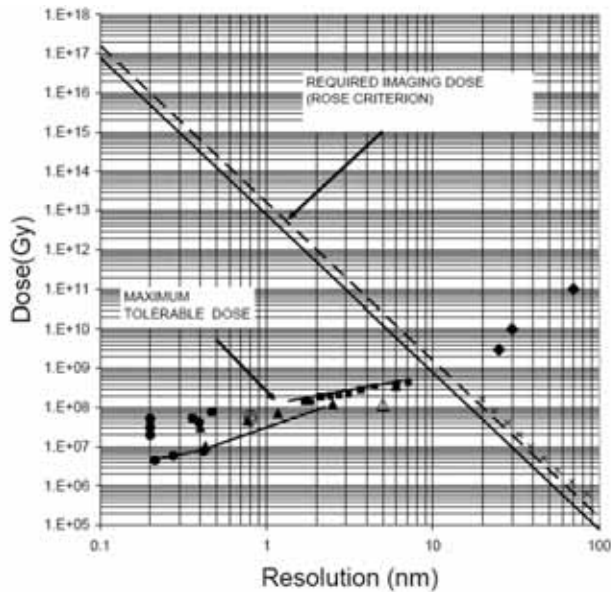
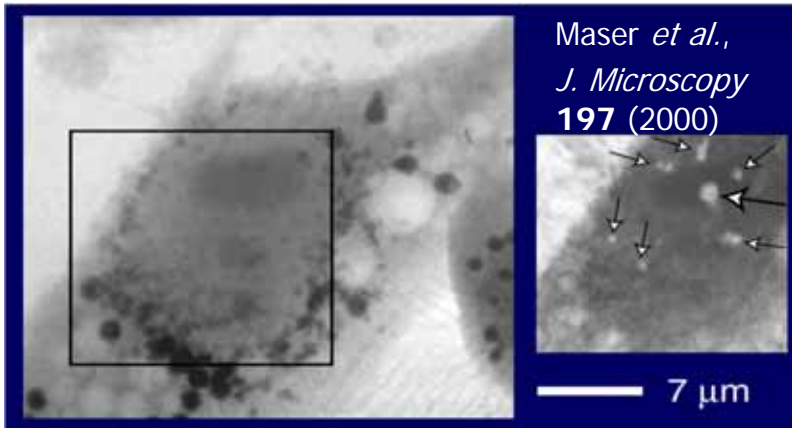


Measured Spot size $25 \times 27 \text{ nm}$, 12 keV

2D Efficiency: 17% at 19.5 keV

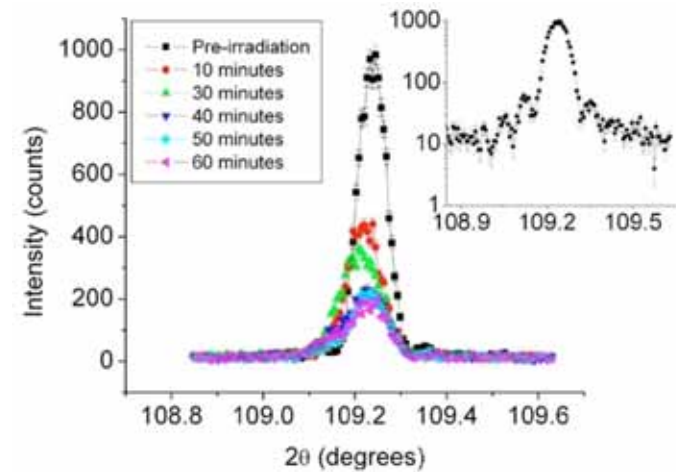
Experimental Considerations: Radiation Damage

- Bio-medical sciences: Dose limit $\sim 10^{10}$ Gy

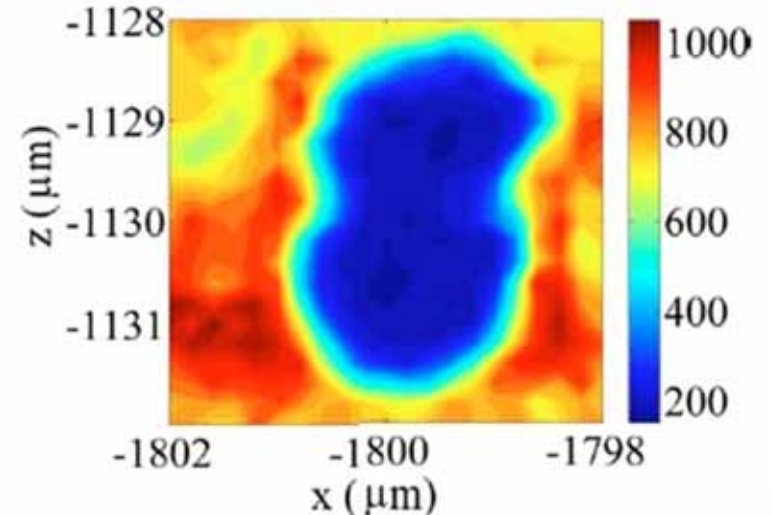


M. Howells et al. 2005

- Materials science: Dose limit?



140 nm SOI Si(800) reflection Total dose: 10^8 Gy



Polvino *et al.*, APL **92**, (2008) APS sector 2 microdiffraction

Experimental considerations for sub-10 nm beams

- Experimental Parameters:
 - Photon Energy: 20 keV
 - Resolution: 5 nm
 - Required monochromaticity: $\Delta E/E = 10^{-5}$
- Focal length: $f = 5 \text{ mm}$ ($D = 60 \text{ um @ } 74 \text{ m}$)
- Depth of focus: $\text{DOF} = 1 \text{ micron @ } 20 \text{ keV}$
- Considerations for future approach:
 - Compact instrument (“Pocket Nanoprobe”)
 - Fluorescence, CDI capabilities
 - Science Thrust:
 - defects in solar cells
 - dopants distributions in nanoelectronics
 - catalysis



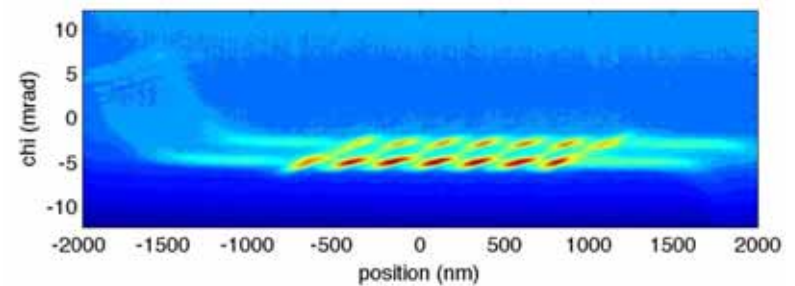
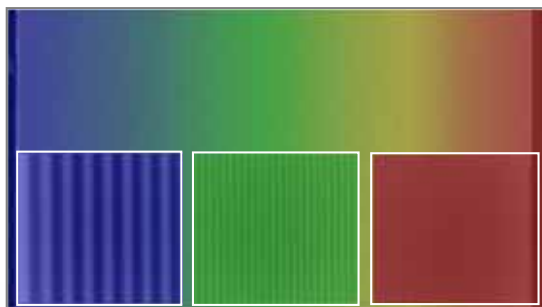
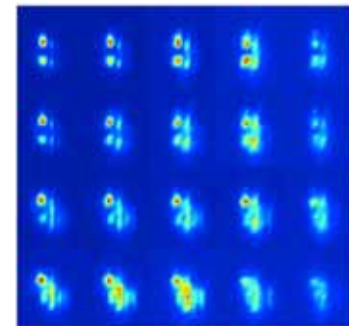
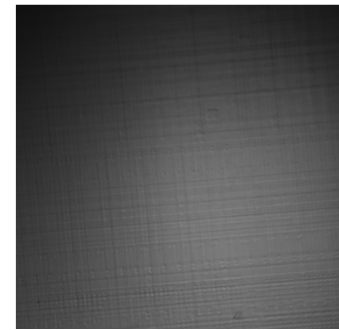
Experimental Considerations for ~ 1 nm beams

- Experimental Parameters (e.g. ERL @ APS):
 - Photon Energy: 10 keV
 - Resolution: 1 nm
 - Required monochromaticity: $\Delta E/E = 10^{-5}$
 - Focal length: $f = 1 \text{ mm}$ ($D = 120 \text{ um @ } 74 \text{ m}$)
 - Depth of focus: $\text{DOF} = 20 \text{ nm}$
 - Power considerations
 - Example ($B = 5 \cdot 10^{21} \text{ Photons/s/mm}^2/\text{mrad}^2/0.1\% \text{BW}$)
 - Focused Photon Flux: $1.5 \cdot 10^{11} \text{ Photons/s}$ ($\Delta E/E = 10^{-5}$)
 - Power absorbed by sample: $2 \cdot 10^{-5} \text{ W}$
 - Sample: Si, $t = 1 \text{ um}$ $\rightarrow \text{PD} = 10^7 \text{ W/mm}^2$
- Significant fundamental issues at 1 nm/ ERL brightness



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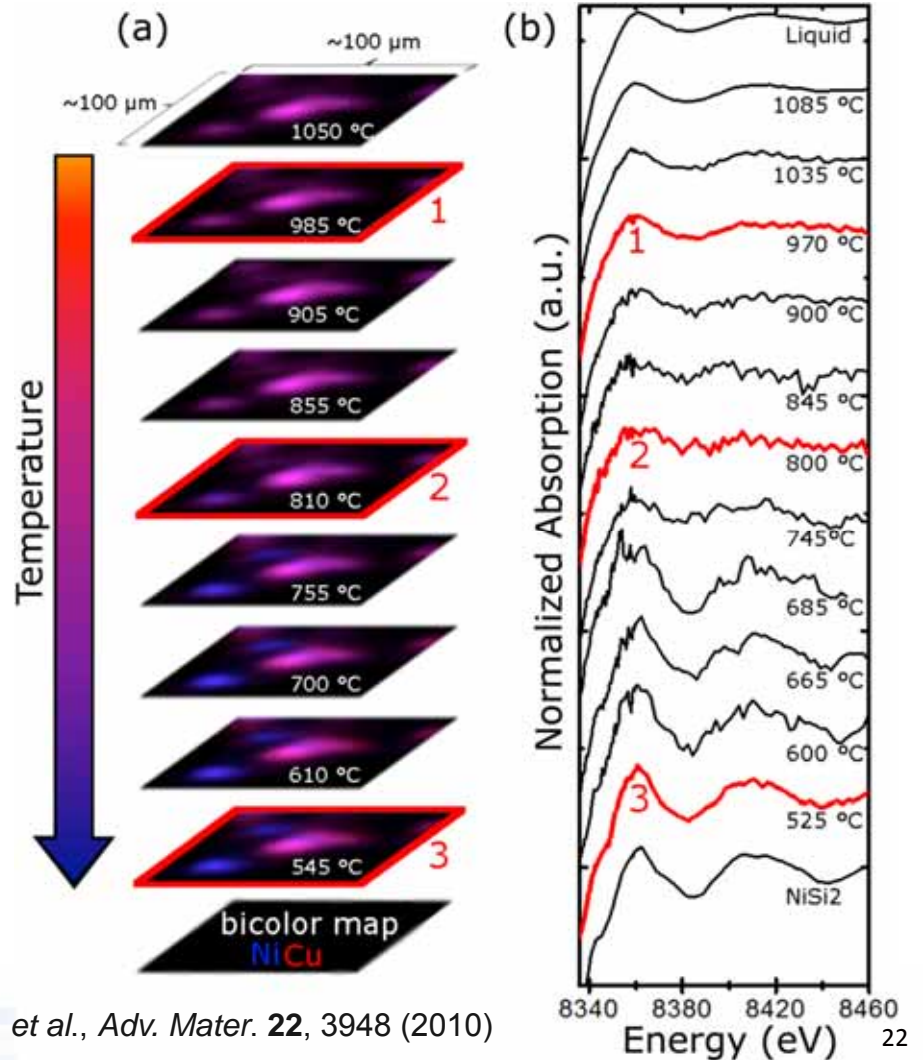
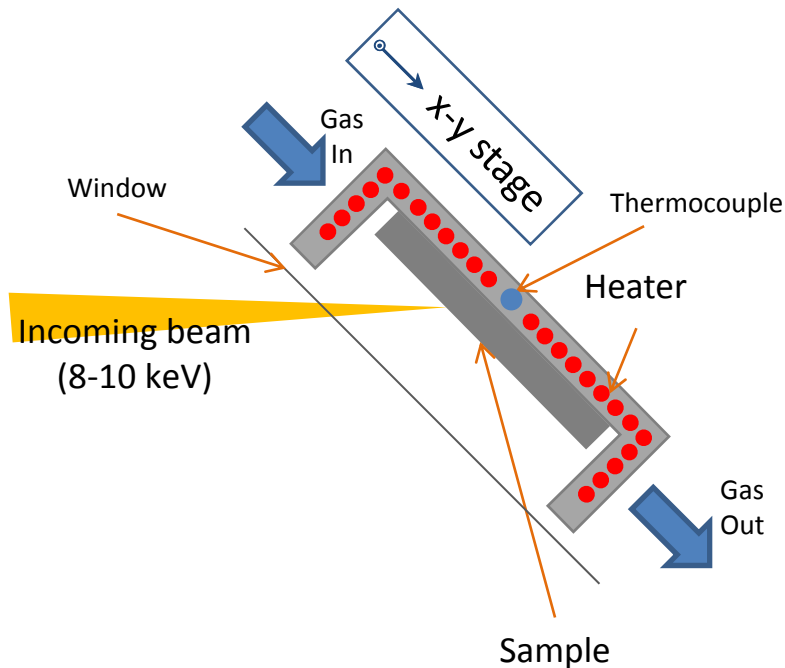
Next Generation Facility: In-situ Nanoprobe Beamline.

Imaging hierarchical structures under Real conditions

- Capabilities: Fast Fluorescence Imaging and Spectroscopy
- Mirror Optics for focusing to 50 nm
 - Accommodates 100x larger bandwidth than diffractive optics
 - 10x focusing efficiency compared to diffractive optics
 - Full spectroscopy
- MLL optics for focusing to 20 nm
 - Good efficiency for hard x-rays
- In-situ capabilities
 - Heating to 1000 ° , cooling to 90 K (LN2), sub-70K (He)
 - Flow of fluids and gases
- Detection channels
 - X-ray fluorescence for elemental mapping and spectroscopy
 - 2D/3D elemental imaging
 - Small angle coherent diffraction to detect defects

Variable-Temperature Nano-Fluorescence Mapping

- Capability: Variable temperature stage from 90 K \rightarrow > 800 °C with nanoprobe
 - Discovery: Thermodynamics and kinetics of defect generation and annihilation



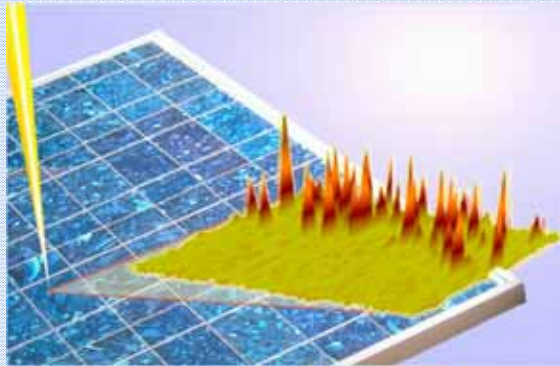
Courtesy T. Buonassisi

Hudelson *et al.*, *Adv. Mater.* **22**, 3948 (2010)



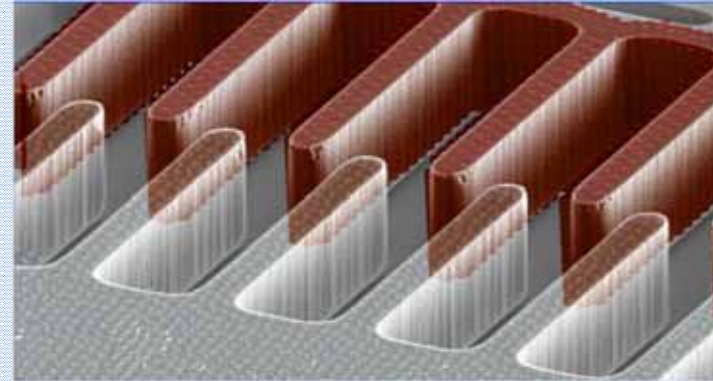
Science Thrust:

Photovoltaics



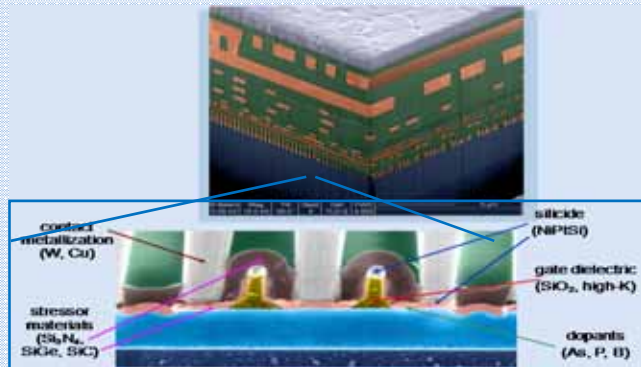
Courtesy T. Buonassisi, MIT

Energy Storage



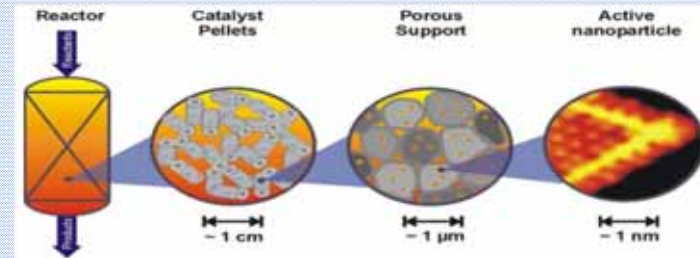
Courtesy T. Rajh, ANL

Nanoscale Electronics



Courtesy C. Murray, IBM

Catalysis



Courtesy G. Mitchell, Dow Chemical



Summary

- **Current Capabilities: CNM/APS Hard X-ray Nanoprobe**
 - Nanoscale Diffraction, fluorescence, tomography at 30 – 50 nm
 - Strain in materials and devices, study of structural phase transitions
 - Structure/composition of geopolymers, biological systems
 - Advanced building materials, energy storage systems
- **Towards Nanofocusing of Hard X-rays**
 - APS Goal: 5 nm focus at 25 keV
 - Nanoscale impurities and contaminants at defects (solar cells, ULK dielectrics)
 - Advanced energy materials (e.g. nanoparticle based battery electrodes, fuel cell materials)
 - Approach: compact MLL microscope/pocket nanoprobe
- **Future: In-Situ Nanoprobe Beamline**
 - 20 nm – 50 nm resolution at 10 – 1000x increased flux
 - In-situ fluorescence spectroscopy, tomography
 - Sensitivity to \ll 100 atoms
 - Coherent scattering to map defects
 - Applications: Photovoltaics, Energy Storage, Nanoscale Electronics, Catalysis, Biomedical applications

